

NCV8403A, NCV8403B

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage Internally Clamped	V_{DSS}	42	Vdc
Gate-to-Source Voltage	V_{GS}	± 14	Vdc
Drain Current Continuous	I_{D}	Internally Limited	
Total Power Dissipation – SOT-223 Version @ $T_A = 25^\circ\text{C}$ (Note 1) @ $T_A = 25^\circ\text{C}$ (Note 2)	P_{D}	1.13 1.56	W
Total Power Dissipation – DPAK Version @ $T_A = 25^\circ\text{C}$ (Note 1) @ $T_A = 25^\circ\text{C}$ (Note 2)		1.32 2.5	
Thermal Resistance – SOT-223 Version Junction-to-Soldering Point Junction-to-Ambient (Note 1) Junction-to-Ambient (Note 2)	$R_{\theta\text{JS}}$ $R_{\theta\text{JA}}$ $R_{\theta\text{JA}}$	12 110 80	$^\circ\text{C/W}$
Thermal Resistance – DPAK Version Junction-to-Soldering Point Junction-to-Ambient (Note 1) Junction-to-Ambient (Note 2)		2.5 95 50	
Single Pulse Inductive Load Switching Energy ($V_{\text{DD}} = 25\text{ Vdc}$, $V_{\text{GS}} = 5.0\text{ V}$, $I_{\text{L}} = 2.8\text{ A}$, $L = 120\text{ mH}$, $R_{\text{G}} = 25\ \Omega$)	E_{AS}	470	mJ
Load Dump Voltage ($V_{\text{GS}} = 0$ and 10 V , $R_{\text{I}} = 2.0\ \Omega$, $R_{\text{L}} = 4.5\ \Omega$, $t_{\text{d}} = 400\text{ ms}$)	V_{LD}	55	V
Operating Junction Temperature	T_{J}	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted onto minimum pad size (0.412" square) FR4 PCB, 1 oz cu.
2. Mounted onto 1" square pad size (1.127" square) FR4 PCB, 1 oz cu.

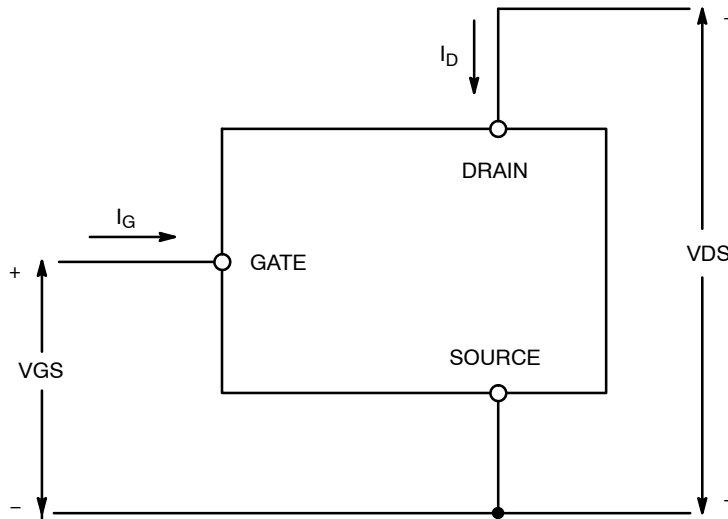


Figure 1. Voltage and Current Convention

NCV8403A, NCV8403B

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Clamped Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 250 μAdc) (V _{GS} = 0 Vdc, I _D = 250 μAdc, T _J = -40°C to 150°C) (Note 3)	V _{(BR)DSS}	42 40	46 45	51 51	Vdc Vdc
Zero Gate Voltage Drain Current (V _{DS} = 32 Vdc, V _{GS} = 0 Vdc) (V _{DS} = 32 Vdc, V _{GS} = 0 Vdc, T _J = 150°C) (Note 3)	I _{DSS}	- -	0.6 2.5	5.0 -	μAdc
Gate Input Current (V _{GS} = 5.0 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	-	50	125	μAdc

ON CHARACTERISTICS

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 1.2 mA) Threshold Temperature Coefficient (Negative)	V _{GS(th)}	1.0 -	1.7 5.0	2.2 -	Vdc mV/°C
Static Drain-to-Source On-Resistance (Note 4) (V _{GS} = 10 Vdc, I _D = 3.0 Adc, T _J @ 25°C) (V _{GS} = 10 Vdc, I _D = 3.0 Adc, T _J @ 150°C) (Note 3)	R _{DS(on)}	- -	53 95	68 123	mΩ
Static Drain-to-Source On-Resistance (Note 4) (V _{GS} = 5.0 Vdc, I _D = 3.0 Adc, T _J @ 25°C) (V _{GS} = 5.0 Vdc, I _D = 3.0 Adc, T _J @ 150°C) (Note 3)	R _{DS(on)}	- -	63 105	76 135	mΩ
Source-Drain Forward On Voltage (I _S = 7.0 A, V _{GS} = 0 V)	V _{SD}	-	0.95	1.1	V

SWITCHING CHARACTERISTICS (Note 3)

Turn-ON Time (10% V _{IN} to 90% I _D)	V _{IN} = 0 V to 5 V, V _{DD} = 25 V I _D = 1.0 A, Ext R _G = 2.5 Ω	t _{ON}	44		μs
Turn-OFF Time (90% V _{IN} to 10% I _D)		t _{OFF}	84		
Turn-ON Time (10% V _{IN} to 90% I _D)	V _{IN} = 0 V to 10 V, V _{DD} = 25 V, I _D = 1.0 A, Ext R _G = 2.5 Ω	t _{ON}	15		
Turn-OFF Time (90% V _{IN} to 10% I _D)		t _{OFF}	116		
Slew-Rate ON (20% V _{DS} to 50% V _{DS})	V _{in} = 0 to 10 V, V _{DD} = 12 V, R _L = 4.7 Ω	-dV _{DS} /dt _{ON}	2.43		V/μs
Slew-Rate OFF (80% V _{DS} to 50% V _{DS})		dV _{DS} /dt _{OFF}	0.83		

SELF PROTECTION CHARACTERISTICS (T_J = 25°C unless otherwise noted) (Note 5)

Current Limit	V _{GS} = 5.0 V, V _{DS} = 10 V V _{GS} = 5.0 V, T _J = 150°C (Notes 3, 6)	I _{LIM}	10 5.0	15 10	20 15	Adc
Current Limit	V _{GS} = 10 V, V _{DS} = 10 V V _{GS} = 10 V, T _J = 150°C (Notes 3, 6)	I _{LIM}	12 8.0	17 13	22 18	Adc
Temperature Limit (Turn-off)	V _{GS} = 5.0 Vdc (Notes 3, 6)	T _{LIM(off)}	150	175	200	°C
Thermal Hysteresis	V _{GS} = 5.0 Vdc	ΔT _{LIM(on)}	-	15	-	°C
Temperature Limit (Turn-off)	V _{GS} = 10 Vdc (Notes 3, 6)	T _{LIM(off)}	150	165	185	°C
Thermal Hysteresis	V _{GS} = 10 Vdc	ΔT _{LIM(on)}	-	15	-	°C

GATE INPUT CHARACTERISTICS (Note 3)

Device ON Gate Input Current	V _{GS} = 5 V I _D = 1.0 A	I _{GON}		50		μA
	V _{GS} = 10 V I _D = 1.0 A			400		
Current Limit Gate Input Current	V _{GS} = 5 V, V _{DS} = 10 V	I _{GCL}		0.1		mA
	V _{GS} = 10 V, V _{DS} = 10 V			0.6		
Thermal Limit Fault Gate Input Current	V _{GS} = 5 V, V _{DS} = 10 V	I _{GTL}		0.45		mA
	V _{GS} = 10 V, V _{DS} = 10 V			1.5		

ESD ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (Note 3)

Electro-Static Discharge Capability	Human Body Model (HBM)	ESD	4000	-	-	V
Electro-Static Discharge Capability	Machine Model (MM)	ESD	400	-	-	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Not subject to production testing.

4. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%.

5. Fault conditions are viewed as beyond the normal operating range of the part.

6. Refer to Application Note AND8202/D for dependence of protection features on gate voltage.



TYPICAL PERFORMANCE CURVES

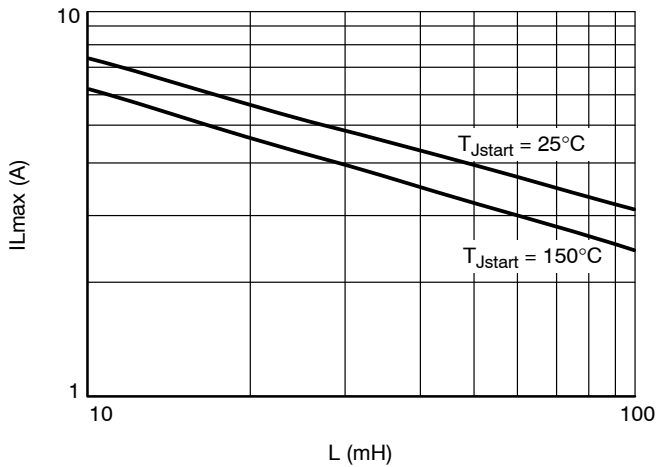


Figure 2. Single Pulse Maximum Switch-off Current vs. Load Inductance

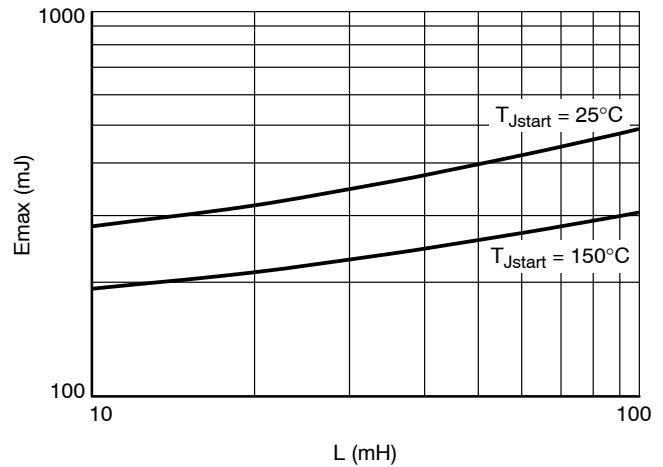


Figure 3. Single-Pulse Maximum Switching Energy vs. Load Inductance

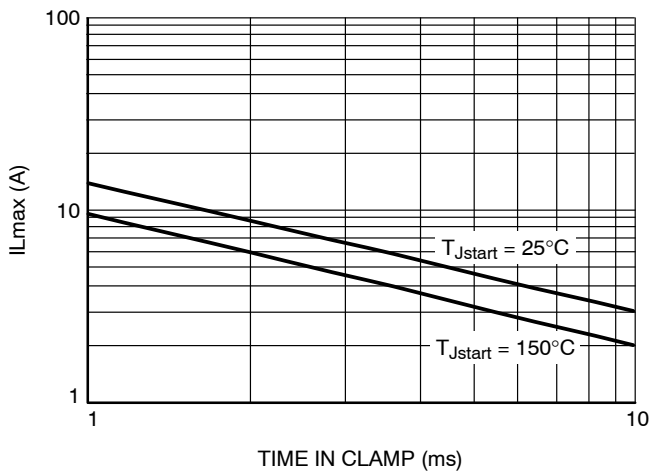


Figure 4. Single Pulse Maximum Inductive Switch-off Current vs. Time in Clamp

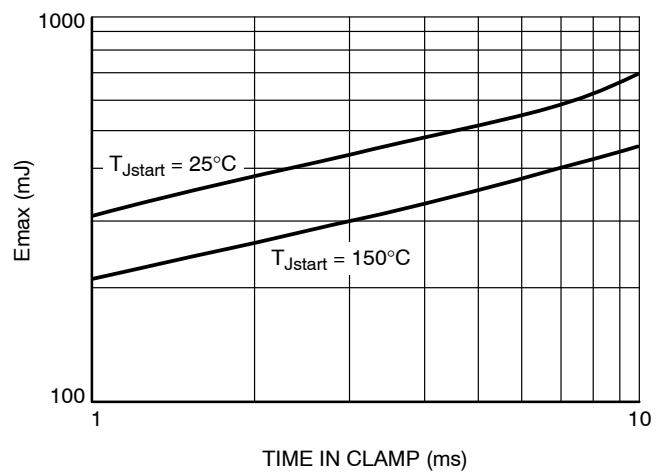


Figure 5. Single-Pulse Maximum Inductive Switching Energy vs. Time in Clamp

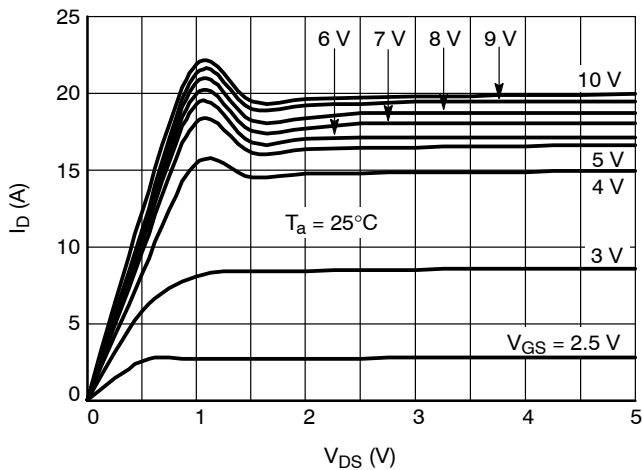


Figure 6. On-state Output Characteristics

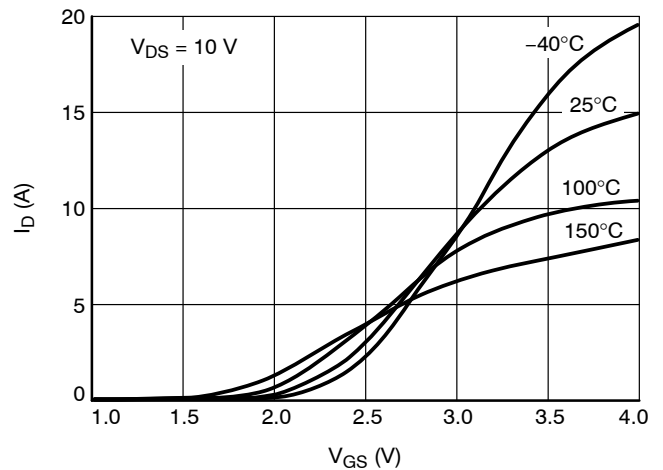


Figure 7. Transfer Characteristics

TYPICAL PERFORMANCE CURVES

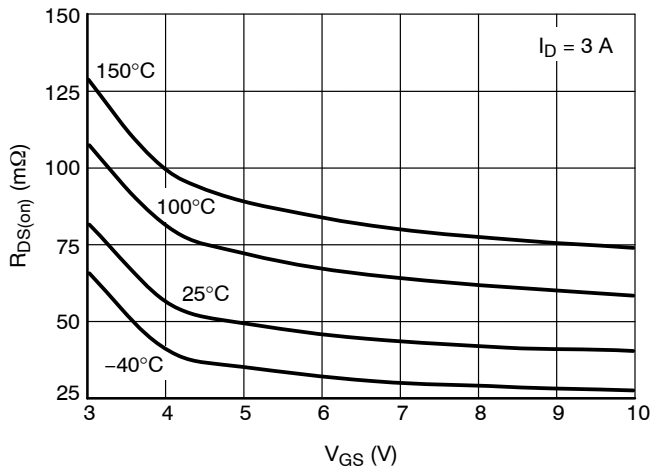


Figure 8. $R_{DS(on)}$ vs. Gate-Source Voltage

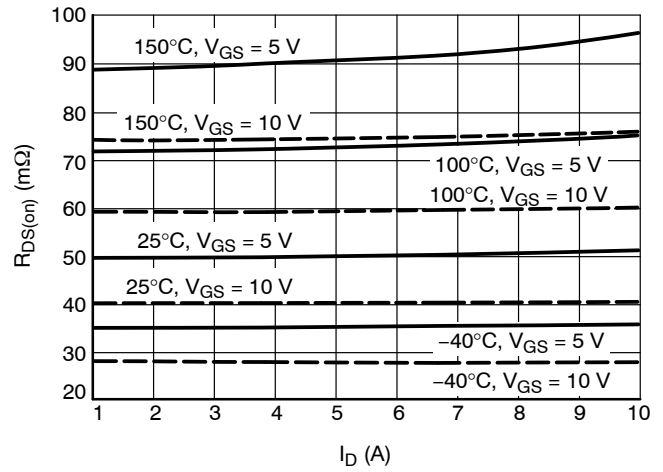


Figure 9. $R_{DS(on)}$ vs. Drain Current

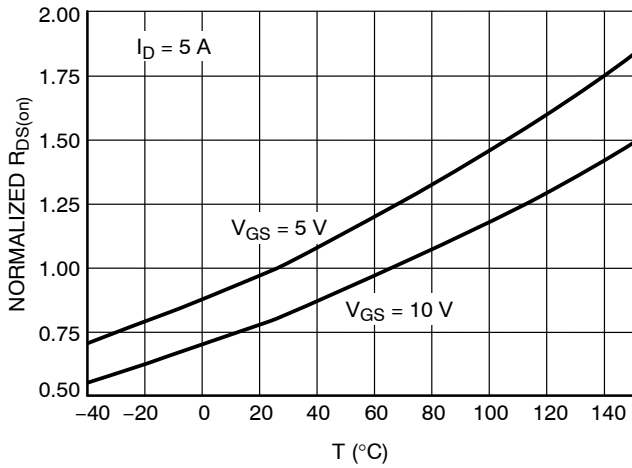


Figure 10. Normalized $R_{DS(on)}$ vs. Temperature

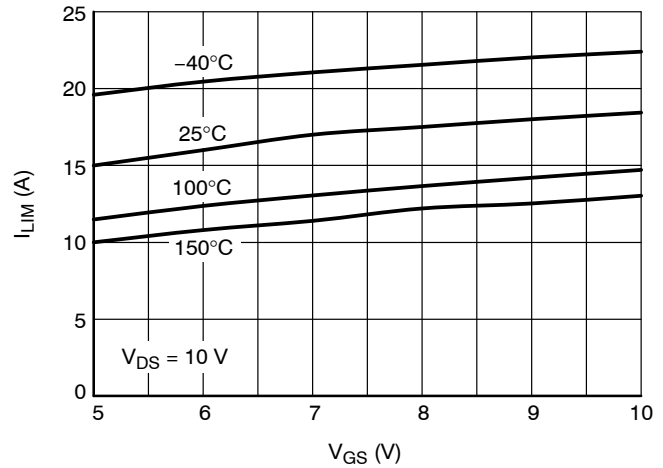


Figure 11. Current Limit vs. Gate-Source Voltage

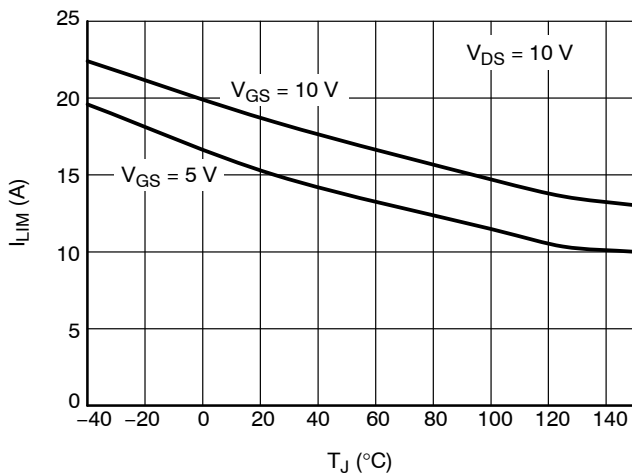


Figure 12. Current Limit vs. Junction Temperature

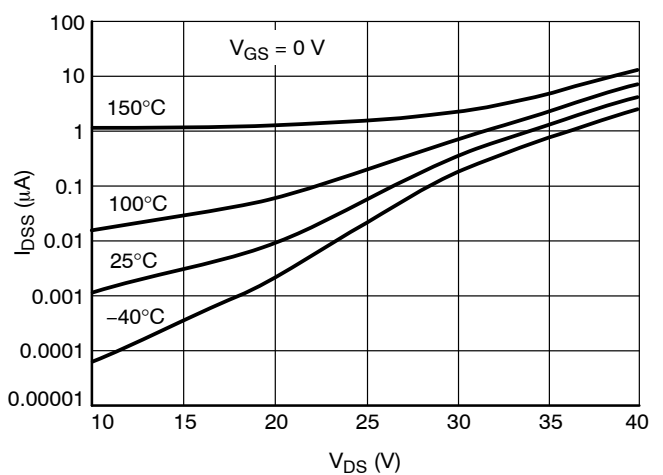


Figure 13. Drain-to-Source Leakage Current

TYPICAL PERFORMANCE CURVES

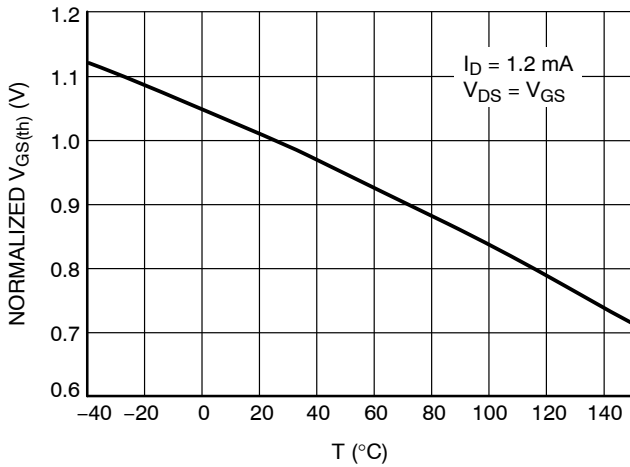


Figure 14. Normalized Threshold Voltage vs. Temperature

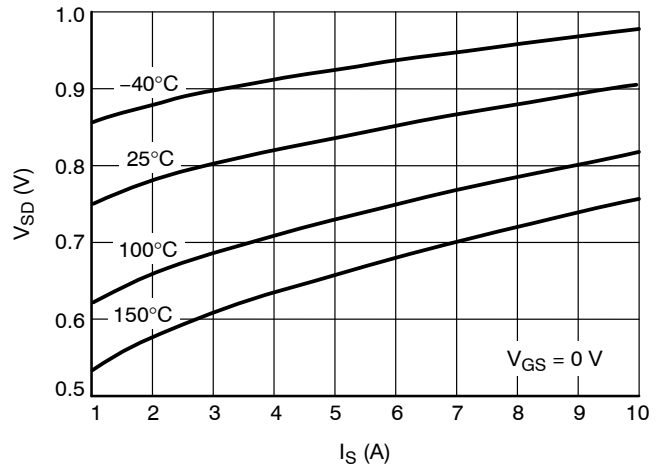


Figure 15. Source-Drain Diode Forward Characteristics

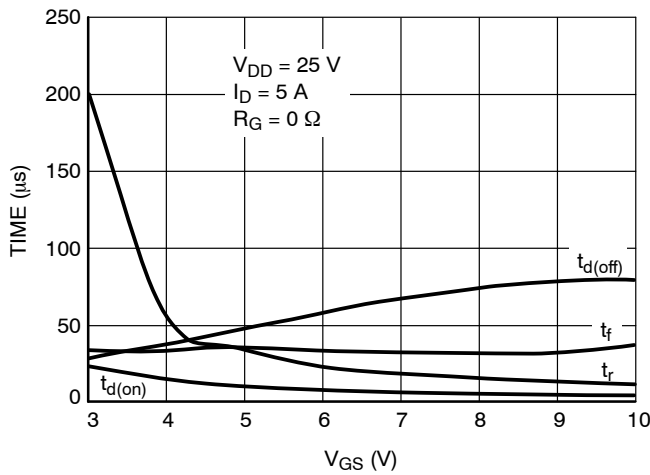


Figure 16. Resistive Load Switching Time vs. Gate-Source Voltage

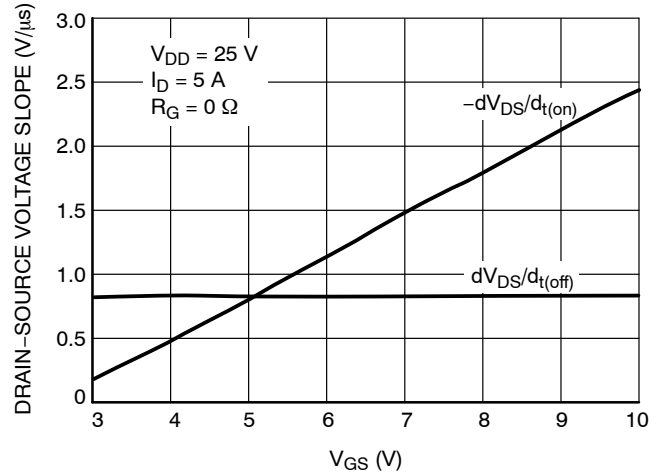


Figure 17. Resistive Load Switching Drain-Source Voltage Slope vs. Gate-Source Voltage

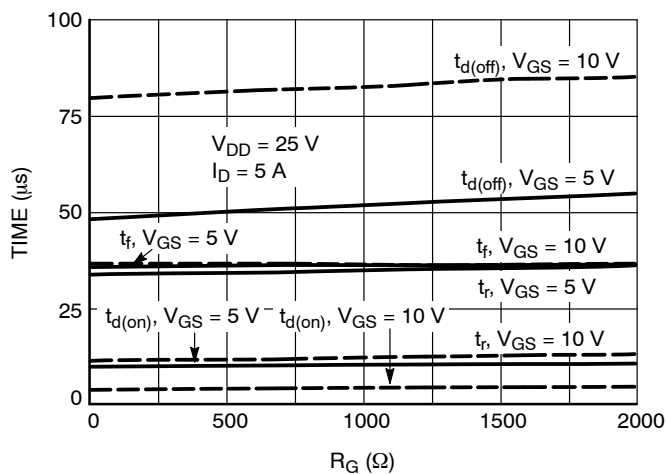


Figure 18. Resistive Load Switching Time vs. Gate Resistance

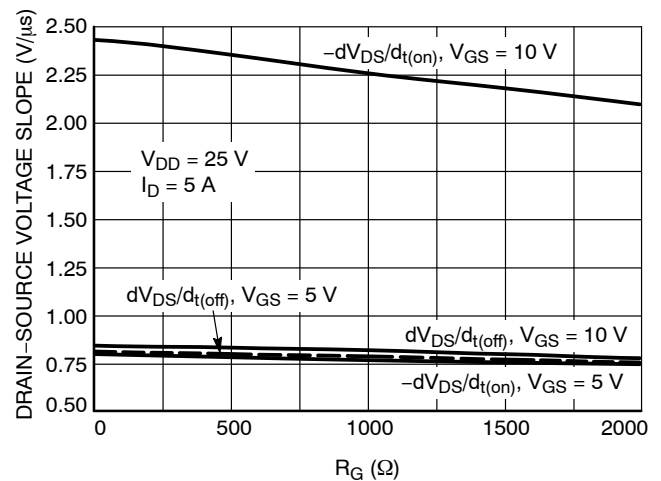


Figure 19. Drain-Source Voltage Slope during Turn On and Turn Off vs. Gate Resistance

TYPICAL PERFORMANCE CURVES

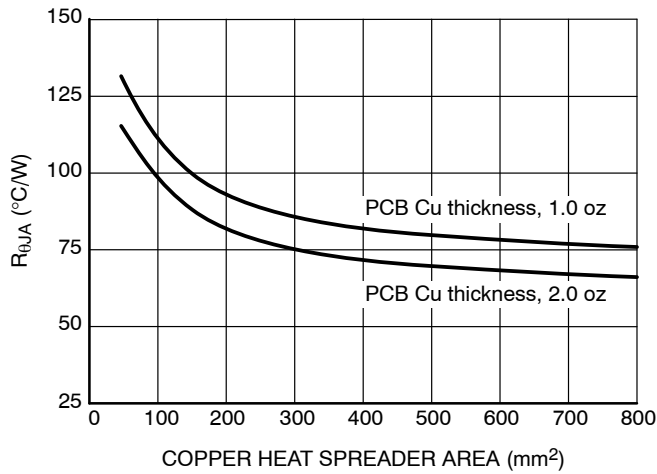


Figure 20. $R_{\theta JA}$ vs. Copper Area – SOT-223

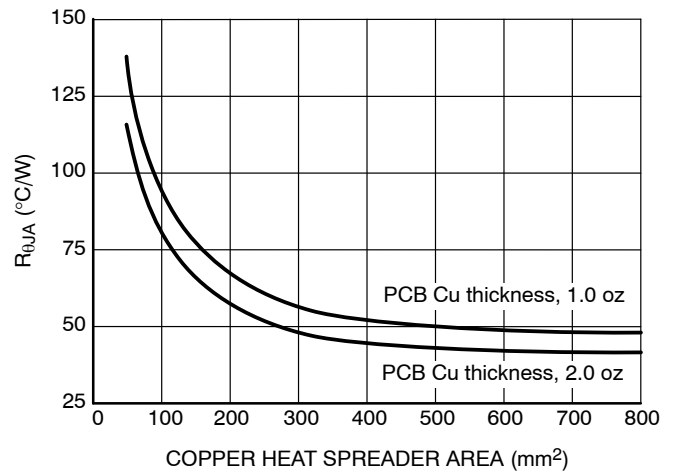


Figure 21. $R_{\theta JA}$ vs. Copper Area – DPAK

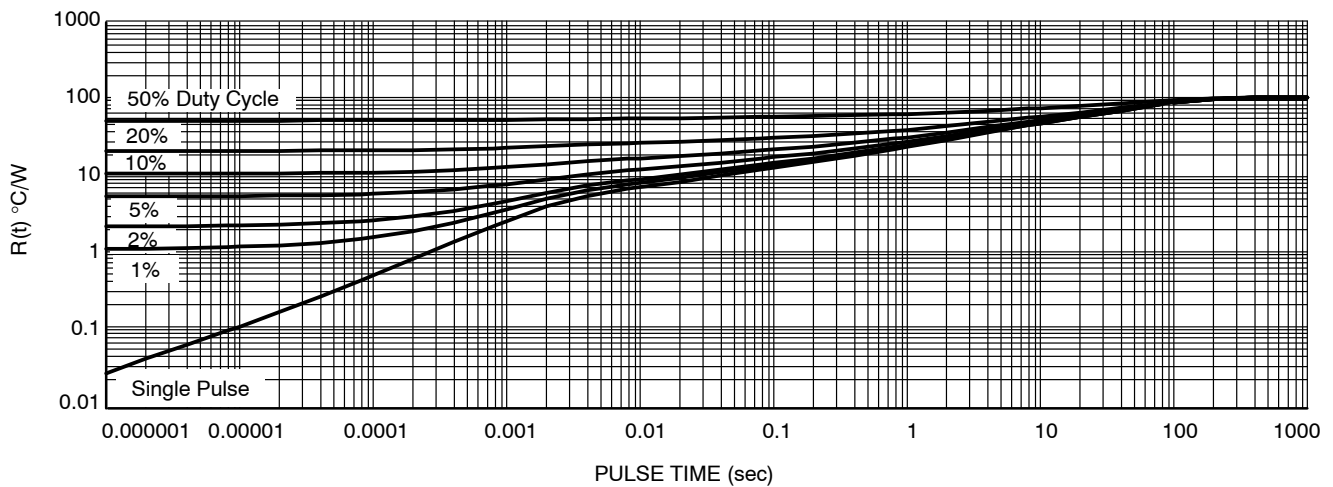


Figure 22. Transient Thermal Resistance – SOT-223 Version

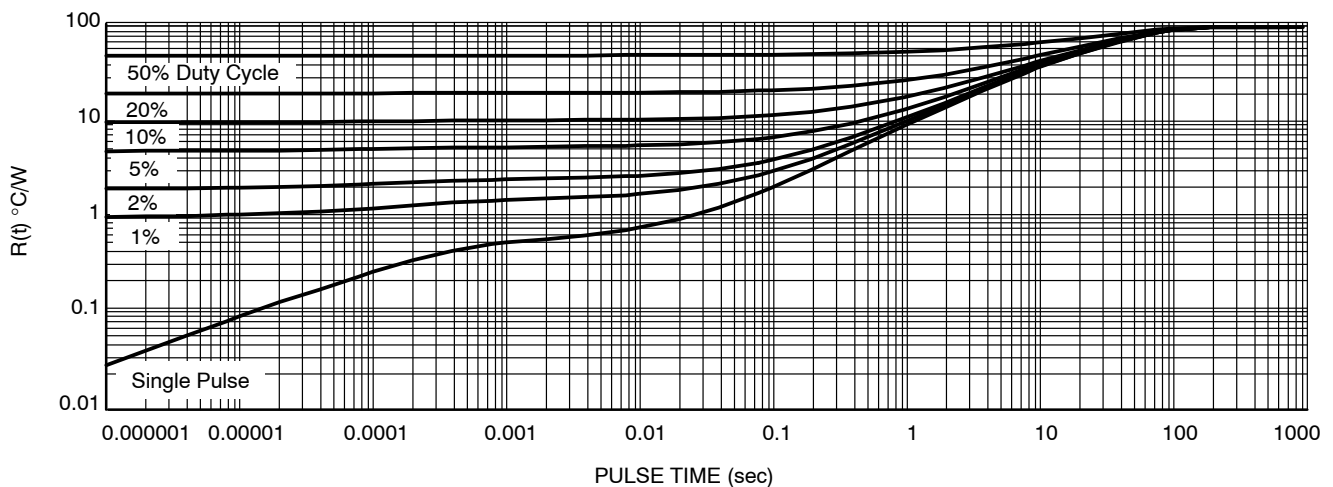


Figure 23. Transient Thermal Resistance – DPAK Version

TEST CIRCUITS AND WAVEFORMS

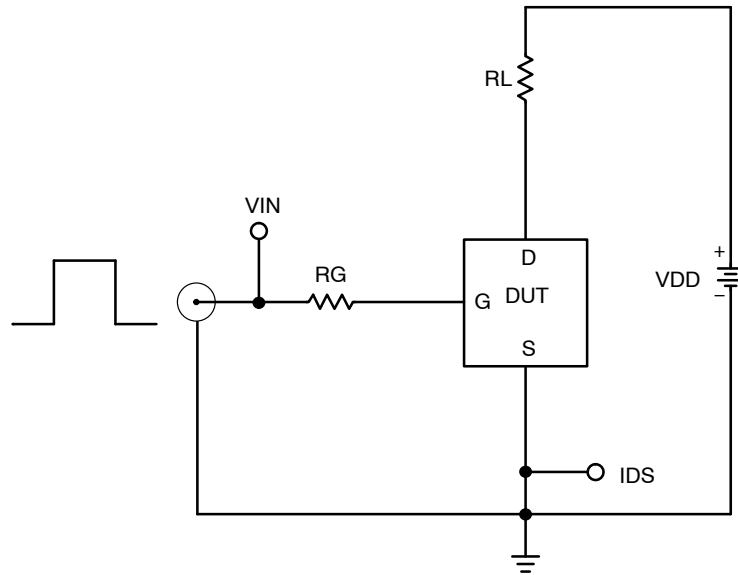


Figure 24. Resistive Load Switching Test Circuit

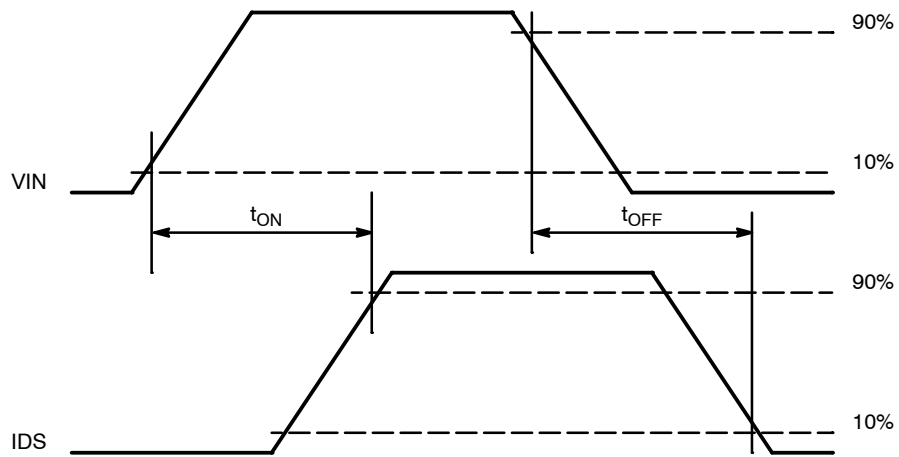


Figure 25. Resistive Load Switching Waveforms

TEST CIRCUITS AND WAVEFORMS

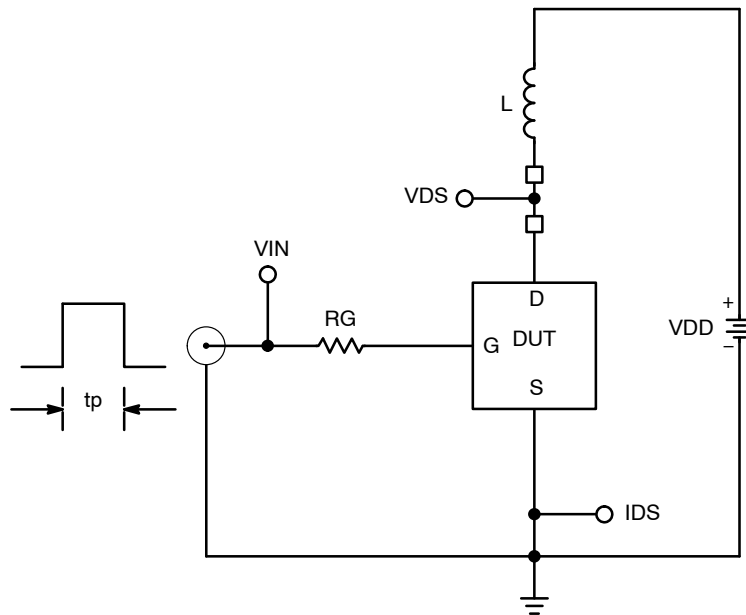


Figure 26. Inductive Load Switching Test Circuit

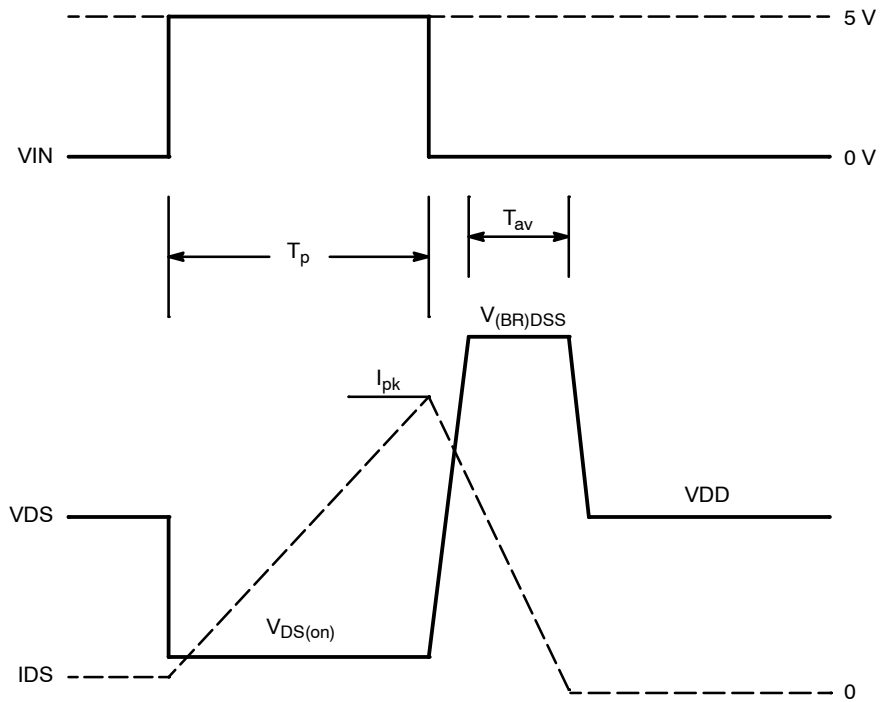


Figure 27. Inductive Load Switching Waveforms

NCV8403A, NCV8403B

ORDERING INFORMATION

Device	Package	Shipping†
NCV8403ASTT1G	SOT-223 (Pb-Free)	1000 / Tape & Reel
NCV8403ASTT3G	SOT-223 (Pb-Free)	4000 / Tape & Reel
NCV8403BDTRKG	DPAK (Pb-Free)	2500 / Tape & Reel

DISCONTINUED (Note 7)

NCV8403ADTRKG	DPAK (Pb-Free)	2500 / Tape & Reel
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†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

7. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

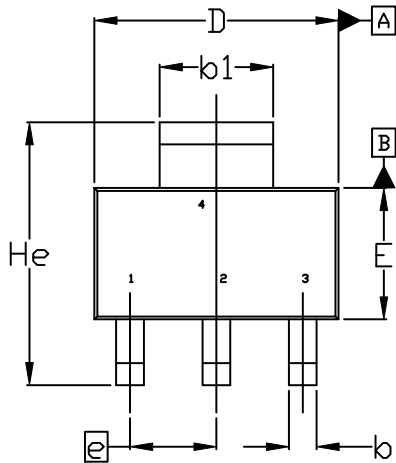




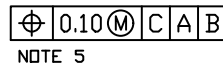
SCALE 1:1

SOT-223 (TO-261)
CASE 318E-04
ISSUE R

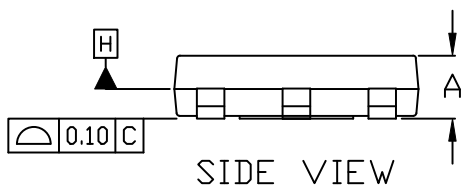
DATE 02 OCT 2018



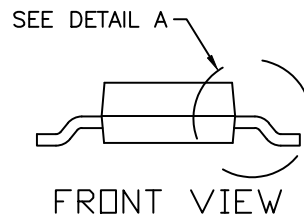
TOP VIEW



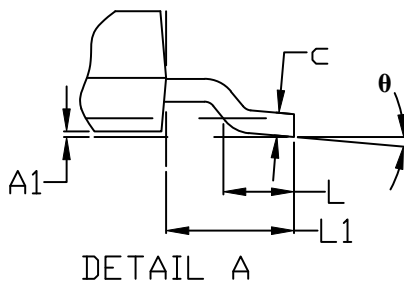
NOTE 5



SIDE VIEW



FRONT VIEW

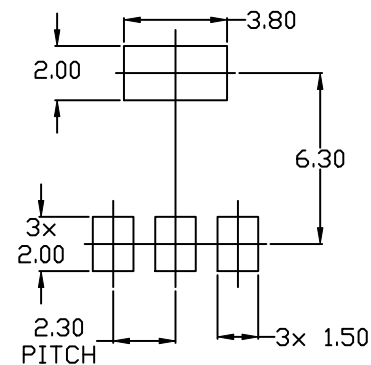


DETAIL A

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
c	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		
L	0.20	---	---
L1	1.50	1.75	2.00
He	6.70	7.00	7.30
θ	0°	---	10°


RECOMMENDED MOUNTING
FOOTPRINT

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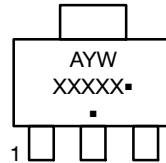
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SOT-223 (TO-261)
CASE 318E-04
ISSUE R

DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

**GENERIC
MARKING DIAGRAM***

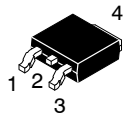


A = Assembly Location
 Y = Year
 W = Work Week
 XXXXX = Specific Device Code
 ▪ = Pb-Free Package

(Note: Microdot may be in either location)
 *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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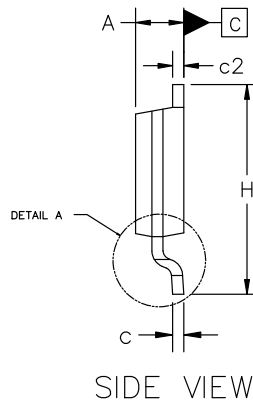
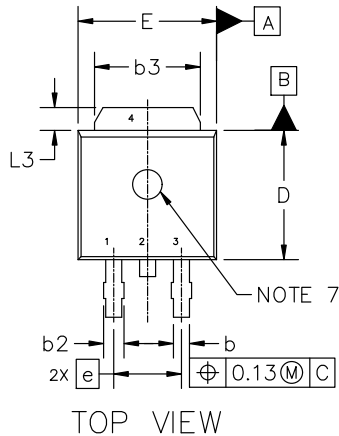
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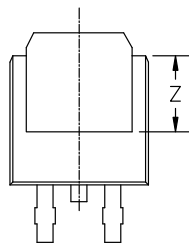
DPAK-3 6.10x6.54x2.28, 2.29P
CASE 369C
ISSUE K

DATE 14 MAY 2026

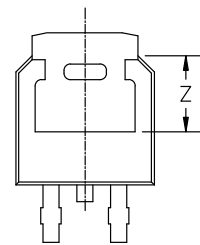
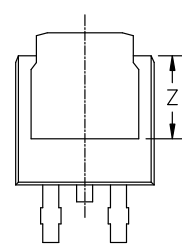
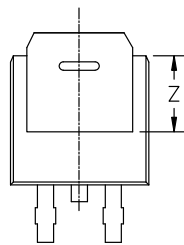
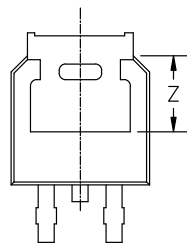
SCALE 1:1



MILLIMETERS			
DIM	MIN	NOM	MAX
A	2.18	2.28	2.38
A1	0.00	---	0.13
b	0.63	0.76	0.89
b2	0.72	0.93	1.14
b3	4.57	5.02	5.46
c	0.46	0.54	0.61
c2	0.46	0.54	0.61
D	5.97	6.10	6.22
E	6.35	6.54	6.73
e	2.29 BSC		
H	9.40	9.91	10.41
L	1.40	1.59	1.78
L1	2.90 REF		
L2	0.51 BSC		
L3	0.89	---	1.27
L4	---	---	1.01
Z	3.93	---	---



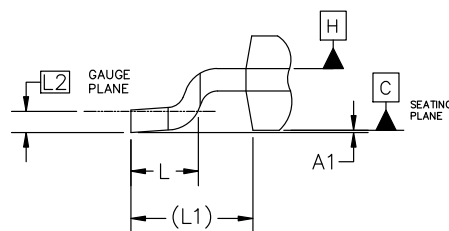
BOTTOM VIEW



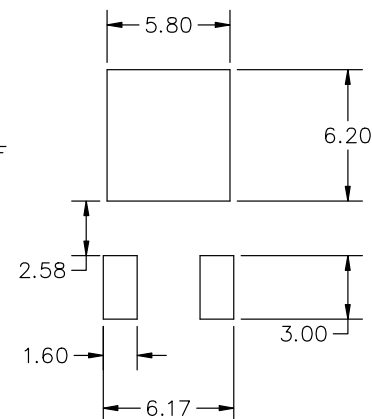
ALTERNATE CONSTRUCTIONS

NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.



DETAIL A
ROTATED 90° CW



RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

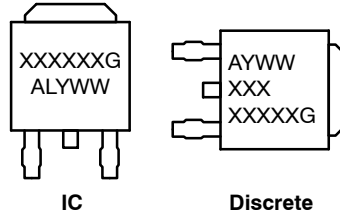
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DPAK–3 6.10x6.54x2.28, 2.29P
 CASE 369C
 ISSUE K

DATE 13 MAY 2026

**GENERIC
 MARKING DIAGRAM***



XXXXXX = Device Code
 A = Assembly Location
 L = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE	STYLE 4: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE	STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE
STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2	STYLE 7: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 8: PIN 1. N/C 2. CATHODE 3. ANODE 4. CATHODE	STYLE 9: PIN 1. ANODE 2. CATHODE 3. RESISTOR ADJUST 4. CATHODE	STYLE 10: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

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